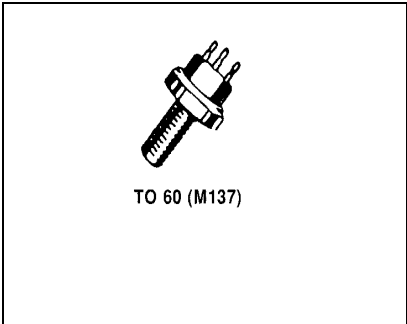


**SD1060**

**RF & MICROWAVE TRANSISTORS**  
**VHF - UHF APPLICATIONS**

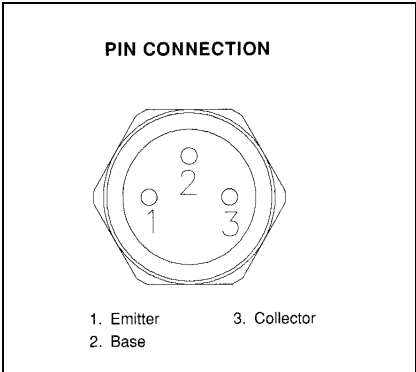
**Features**

- 400 MHz
- 28 VOLTS
- P<sub>OUT</sub> = 5.0 WATTS
- G<sub>P</sub> = 4.7 dB MINIMUM
- COMMON EMITTER CONFIGURATION



**DESCRIPTION:**

This silicon epitaxial NPN planar high frequency transistor employs a multi emitter electrode design. This feature together with a heavily diffused base matrix located between the individual emitters results in high RF current handling capability, high power gain, low base resistance and low output capacitance. These transistors are intended for Class A, B, or C amplifier, oscillator or frequency multiplier circuits and are specifically designed for operation in the VHF-UHF region.



**ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	65	V
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Device Current	1.5	A
P <sub>DISS</sub>	Power Dissipation	11.6	W
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

**Thermal Data**

R <sub>TH(J-C)</sub>	Junction-case Thermal Resistance	15.1	°C/W
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**ELECTRICAL SPECIFICATIONS (Tcase = 25°C)**

**STATIC**

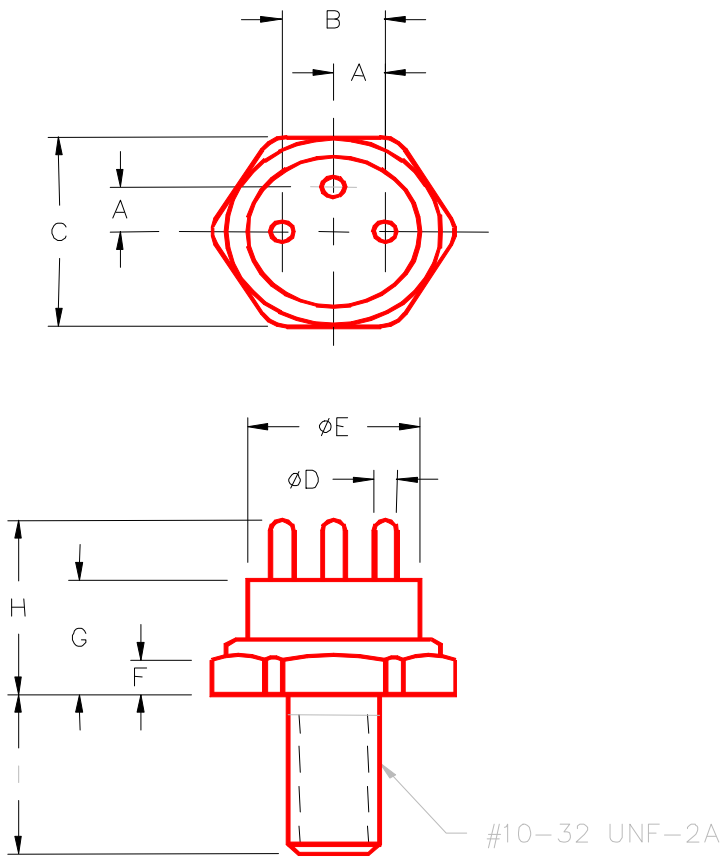
Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
<b>BV<sub>CBO</sub></b>	<b>I<sub>C</sub> = 100 μA</b>	<b>65</b>	---	---	<b>V</b>
<b>BV<sub>EBO</sub></b>	<b>I<sub>E</sub> = 1 mA</b>	<b>4.0</b>	---	---	<b>V</b>
<b>BV<sub>CEO</sub></b>	<b>I<sub>C</sub> = 200 mA</b>	<b>40</b>	---	---	<b>V</b>
<b>I<sub>CEO</sub></b>	<b>V<sub>CE</sub> = 30 V</b>	---	---	<b>0.1</b>	<b>mA</b>

**DYNAMIC**

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
<b>P<sub>OUT</sub></b>	<b>f = 400 MHz    P<sub>IN</sub> = 1.7 W    V<sub>CC</sub> = 28 V</b>	<b>5.0</b>	---	---	<b>W</b>
<b>G<sub>P</sub></b>	<b>f = 400 MHz    P<sub>IN</sub> = 1.7 W    V<sub>CC</sub> = 28 V</b>	<b>45</b>	---	---	<b>%</b>
<b>IMD</b>	<b>f = 400 MHz    P<sub>IN</sub> = 1.7 W    V<sub>CC</sub> = 28 V</b>	<b>4.7</b>	---	---	<b>dB</b>
<b>C<sub>OB</sub></b>	<b>f = 1 MHz    V<sub>CB</sub> = 30 V</b>	---	---	<b>10.0</b>	<b>pF</b>

**PACKAGE MECHANICAL DATA**

PACKAGE STYLE M137



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.090/2,29	.110/2,79	I	.420/10,67	.455/11,56
B	.185/4,70	.215/5,46	I	.140/3,56	.160/4,06
C	.420/10,67	.440/11,18			
D	.030/0,76	.046/1,17			
E	.320/8,13	.360/9,14			
F	.090/2,29	.135/3,43			
G	.215/5,46	.320/8,13			
H		.480/12,19			

STANDARD STUD  
 SHORT STUD